Effect of Ni-Doping on the Optical and Electrical Properties of Tin Oxide Thin Films Deposit by Spray Pyrolysis Method

Md. Rubel Sarkar¹, Mst. Halima Khatun¹, M. K. R. Khan², Md. Shahjahan¹

¹Department of Electronics and Telecommunication Engineering, Bangabandhu Sheikh Mujibur Rahman Science and Technology University, Gopalganj-8100, Bangladesh
²Department of Physics, Rajshahi University, Rajshahi-6205, Bangladesh

Corresponding Author’s e-mail address: shir99[at]yahoo.com

Abstract: In this study, un-doped and Ni-doped SnO₂ have been prepared on glass substrate by low cost spray pyrolysis technique. The films were deposited at a temperature of 350°C using starting materials of SnCl₂.H₂O and NiCl₂.H₂O in air ambient. To study the effect of Ni doping on SnO₂ the samples were characterized by using various techniques like XRD, SEM, UVIR Spectrophotometer and Hall effect measurement. Ni has been doped upto 9% and found that the optical transparency decreases from 84% to 72% with the increase of Ni concentration. The optical band gap of the fabricated samples was found to decrease from 3.55 eV to 3.50 eV for un-doped and 9% Ni-SnO₂. It is observed from the XRD study that the films are polycrystalline in nature. Hall Effect measurement shows that the films are n-type in nature and it is observed that the carrier concentration increases with the doping concentration.

Keywords: Ni-doped SnO₂, Band gap, Carrier concentration, Hall mobility

1. Introduction

Transparent conducting oxides (TCO) have been attracted much attention in the research area over the last decade due to their interesting properties like high electrical conductivity and optical transparency. These properties make them suitable for various applications such as photovoltaic applications. Transparent oxides like In₂O₃, ZnO₂, SnO₂, TiO₂, CdO etc. have various applications in optoelectronic devices, green energy devices, smart sensors, high temperature electron devices[1-3]. Among these oxides SnO₂ has attracted more attention due to ease of fabrication, good adhesion to substrate, stability, low deposition temperature and low starting material costs. Although, their high transparency and low band gap energy, the electrical conductivity is not sufficient enough to use as photovoltaic and other applications. To improve the electrical conductivity many materials are used as dopant like In, Co, Al, Fe, Cu, F, Ni etc. with SnO₂ [4]. A variety of deposition techniques such as reactive electron beam evaporation [5], DC magnetron sputtering [6], reactive thermal deposition [7], spray pyrolysis technique [8-9], sol gel technique [10] have been used for SnO₂ thin films preparation. Among these techniques spray pyrolysis has some advantages such as low cost, lower temperature and air ambient deposition, large area deposition and convenient to control the deposition conditions and possible to deposit homogeneous and smooth films. In this work Ni doped SnO₂ has been fabricated on glass substrate using spray pyrolysis technique and studied optical and electrical properties.

2. Experimental Details

Ni-doped SnO₂ thin films have been prepared by low cost spray pyrolysis technique. Tin chloride (SnCl₂.H₂O) and Nickel chloride6-hydrate (NiCl₂.H₂O) are used for precursor solutions. Samples are prepared with 0.07M concentration. Both materials are dissolved with distilled water and ethanol at 1:1 ratio. In this investigation, SnO₂ films were prepared with various amount of Ni (0%, 1%, 5% and 9%) doping concentration. In spray pyrolysis technique, precursor solutions were supplied from a solution container and sprayed through a nozzle with compressed air. The solutions were sprayed uniformly over the entire substrate at a rate of 0.4 ml/min.

After deposition the films were investigated using several techniques. Optical transmittance and absorbance studies were performed using UV-VIS spectrophotometer (UV-1601, SHIMADZU, Japan). Structural study was performed using X-ray diffraction (XRD) and surface morphology was studied by SEM. Resistivity of the films has been measured within the temperature range 320 K to 370 K using Van der Pauw configuration and Hall measurement is performed to reveal the type of the semiconductor.

3. Results and Discussion

Structural study:

Structural properties of the deposited Ni:SnO₂ films are studied by X-ray diffraction (XRD). Figure 1 shows the XRD pattern of the Ni:SnO₂ films deposited on glass substrate by spray pyrolysis technique. The XRD pattern was taken with Cu-Kα radiation of wavelength λ=1.5405 Å with anode voltage 30 kV, current 10 mA within 20 values 20° to 60°. From the figure it is observed that the films are polycrystalline in nature. Four diffraction peaks are obtained for the characteristic planes (110), (101), (200) and (211) with a tetragonal unit cell which are in agreement with the standard JCPDS data (Card No. 88-0287).
Intensity (a.u.)

From scanning Surface excess might decreases in dimension. Calculated the full Debye Crystallite Ni = 1.5405 (wt %) (110) (101) (211) (200)

Figure 1: XRD output waveform for both Ni-dope and undoped SnO_2 thin films

Crystallite size of the SnO_2 samples were calculated using Debye Scherer formula [11],

\[ D = \frac{k\lambda}{\beta\cos\theta} \]

Where, \( \lambda \) is the wavelength of radiation used (Cu-K_\alpha, \( \lambda = 1.5405 \) Å), \( k \) is the Scherrer constant (\( k = 0.94 \) is used), \( \beta \) is the full width at half maximum (FWHM) intensity of the diffraction peak for which the crystallite size is to be calculated, \( \theta \) the diffraction angle and \( D \) the crystallite dimension. The crystallite size, lattice spacing (d), and lattice constant (a) determined from the main peak are summarized in the table-1 below. It is observed that the crystallite size decreases with Ni doping incorporation in SnO_2 films which might be due to the strain introduced in the samples due to excess Ni interstitials in the samples.

### Table 1: Structural parameters of Ni-doped SnO_2

<table>
<thead>
<tr>
<th>Ni-doping (wt %)</th>
<th>(h k l)</th>
<th>Lattice spacing (Å)</th>
<th>Average crystallite size, D (nm)</th>
<th>Average lattice constant, a (Å)</th>
</tr>
</thead>
<tbody>
<tr>
<td>0</td>
<td>(110)</td>
<td>3.35</td>
<td>18.20</td>
<td>3.5362</td>
</tr>
<tr>
<td>1</td>
<td>(110)</td>
<td>3.35</td>
<td>17.31</td>
<td>3.5573</td>
</tr>
<tr>
<td>5</td>
<td>(110)</td>
<td>3.37</td>
<td>17.64</td>
<td>3.4911</td>
</tr>
<tr>
<td>9</td>
<td>(110)</td>
<td>3.37</td>
<td>16.67</td>
<td>3.5650</td>
</tr>
</tbody>
</table>

Surface morphology of the deposited samples were studied by scanning electron microscope and illustrated in Figure 2. From the figure it is observed that the film surfaces are rough and the roughness increases with the Ni-doping. Moreover, some spikes like structure are found in Ni-doped SnO_2 films as shown in Figure 2 (b).

Figure 2: SEM images of (a) undoped SnO_2 and (b) Ni doped SnO_2.

**Optical Properties:**

Optical properties of SnO_2 and Ni:SnO_2 thin films

Figure 3(a) and Figure 3(b) show the transmittance and absorbance spectra of the undoped and Ni-doped SnO_2 thin films as a function of wavelength range 300 nm to 1100 nm. It is observed that the optical transmittance is very high up to 84% in the visible region for undoped SnO_2. A sharp increase in transmittance is observed at around 350 nm and attributed to the band edge absorption. But the transparency decreases with the increase of the amount of Ni doping concentration. At 9% Ni concentration, the transparency falls to 72%. This may due to be the effect of scattering of photons due to the defects produced by the Ni atoms in the SnO_2.
The absorption spectra of Ni doped SnO₂ are illustrated in Figure 3(b). It is observed that the absorbance of the films is high at the band edge and decreased sharply. After the band edge wavelength, the absorbance observed almost constant over the higher wavelength region. It is also seen that the absorbance increases with the increase of Ni doping concentration.

The absorption coefficients of the Ni-doped SnO₂ are studied as shown in the Figure 4. The absorption coefficient (α) has been calculated as follows [12],

\[ \alpha = \frac{1}{t} \ln \left( \frac{I_0}{I} \right) \]  \hspace{1cm} (2)

Where, t is the film thickness and T is the transmission coefficient of film.

Absorption coefficient decreases with the increase of wavelength because at higher wavelength the photons have lower energy hence mainly transmitted up to band gap energy is not exceeded [4].

Figure 5 demonstrates that the skin depth is dependent on the wavelength and increases with the increase of wavelength. Skin depth determined from absorption coefficient values and it inversely proportional to the absorption coefficient. In this investigation, films skin depth, \( \chi \) has been calculated by,

\[ \chi = \frac{1}{\alpha} \]  \hspace{1cm} (3)

Here, \( \alpha \) is absorption coefficient. Skin depth is useful in analyzing transmission characteristics. High skin depth material has lower conductivity. Pure SnO₂ film has higher skin depth but its value decreases with the incorporation of Ni into SnO₂ film. This result is supported by the electrical measurement which shows that the electrical conductivity increases with the increase of Ni doping.
carriers in Ni:SnO$_2$ thin films than un-doped SnO$_2$. Therefore, Ni:SnO$_2$ films show lower transparency because incident light absorbed by the highly charge carriers films surface and hence lower transparent films unveil slightly higher absorbance than pure SnO$_2$ film.

### Electrical properties:

Temperature dependent resistivity of Ni:SnO$_2$ films have been studied by four-probe Vander Pauw’s method in air ambient. Figure 8 illustrates conductivity of SnO$_2$ films deposited on glass substrate. It is observed that the conductivity of the films increases with the increase of temperature indicates semiconducting nature of the SnO$_2$ films. Moreover, the resistivity of the films decreases with the increase of doping concentration. Both the resistivity and sheet resistance decrease with the increase of charge carriers due to the increase of Ni concentration.

![Figure 8: Variation of conductivity with temperature for undoped and Ni:SnO$_2$ thin films.](image)

### Optical properties:

Optical energy band gap of Ni-doped SnO$_2$ thin films have been determined by using Tauc’s relation [14]

$$a h \nu = A (h \nu - E_g)^n$$

Where $a$ is the absorption coefficient, $A$ is an energy independent constant, $h \nu$ is the photon energy and $E_g$ is the optical energy band gap and $n$ is an index related to the density of states for the energy band. Figure 7 shows the variation of $(a h \nu)^2$ as a function of photon energy, $h \nu$. The band gaps of the samples are obtained from the intercepts of energy axis after extrapolation of the straight line of the slope of the curve to zero.

![Figure 7: Variation of $(a h \nu)^2$ with photon energy for undoped and Ni:SnO$_2$ thin films.](image)

It is observed that the band gap energy is due to direct transition and decreases with the increase of doping concentration. The estimated bandgap energies depending on the doping concentration vary from 3.50 eV to 3.53 eV. It was observed tin oxide doped with different concentration of Ni, band gap increases by increasing doping concentration of Ni. Similar results were obtained by Syed Zafar et. al., [15].
Various Hall measurement parameters such as Hall constant ($R_h$), Carrier concentration (N), Resistivity and Hall mobility ($\mu_H$) have been determined as shown in Figure 10 for undoped and doped SnO$_2$ films. The hall measurement reveals the n-type nature of the Ni:SnO$_2$ films. The obtained values are suitable for photovoltaic applications.

4. Conclusion

Undoped SnO$_2$ and Ni:SnO$_2$ thin films deposited on a glass substrate by spray pyrolysis technique at temperature around 320–330°C. Homogeneous and uniform films are obtained in this technique on the glass substrate. It is observed that film transparency decreases and optical band gap energy increases with the increase of the amount of Ni in the SnO$_2$ films. XRD investigation shows the polycrystalline nature of the deposited samples. Crystallite size decreases after Ni incorporation in SnO$_2$. Electrical measurement exposes that films conductivity increases with Ni doping. Carrier concentration and hall mobility augmented by incorporation of Ni which sort out by hall experiment.

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References